

Surface Mount Schottky Barrier Rectifier
 Reverse Voltage - 100 V
 Forward Current - 1.0A

PINNING

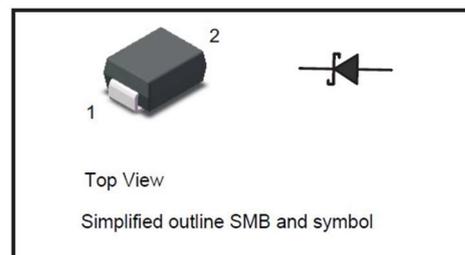
PIN	DESCRIPTION
1	Cathode
2	Anode

Features

- Metal silicon junction, majority carrier conduction
- For surface mounted applications
- Low power loss, high efficiency
- High forward surge current capability
- For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications

MECHANICAL DATA

- Case: SMB
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 70mg / 0.0025oz


Absolute Maximum Ratings and Electrical characteristics

Ratings at 25 °C ambient temperature unless otherwise specified. Single phase, half wave, 60Hz resistive or inductive load, for capacitive load, derate by 20 %

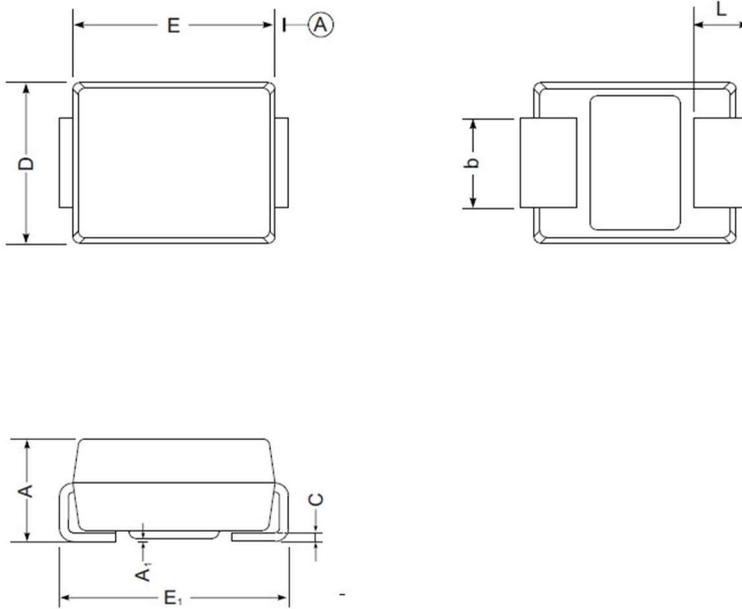
Parameter	Symbols	10BQ100	Units
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	100	V
Maximum RMS voltage	V_{RMS}	70	V
Maximum DC Blocking Voltage	V_{DC}	100	V
Maximum Average Forward Rectified Current at $T_c = 100\text{ }^\circ\text{C}$	$I_{F(AV)}$	1.0	A
Peak Forward Surge Current, 8.3ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I_{FSM}	25	A
Max Instantaneous Forward Voltage at 1 A	V_F	0.85	V
Maximum DC Reverse Current $T_a = 25^\circ\text{C}$ at Rated DC Reverse Voltage $T_a = 100^\circ\text{C}$	I_R	0.2 5	mA
Typical Junction Capacitance ⁽¹⁾	C_j	80	pF
Typical Thermal Resistance ⁽²⁾	$R_{\theta JA}$	90	$^\circ\text{C/W}$
Operating Junction Temperature Range	T_j	-55 ~ +150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 ~ +150	$^\circ\text{C}$

(1) Measured at 1MHz and applied reverse voltage of 4 V D.C.

(2) P.C.B. mounted with 2.0" X 2.0" (5 X 5 cm) copper pad areas

PACKAGE OUTLINE

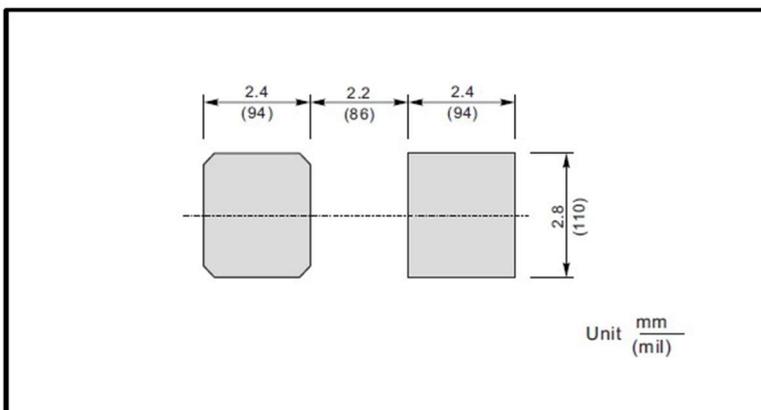
Plastic surface mounted package; 2 leads



SMB mechanical data

UNIT		A	E	D	E ₁	A ₁	L	C	b
mm	max	2.44	4.70	3.94	5.59	0.20	1.5	0.305	2.2
	min	2.13	4.06	3.3	5.08	0.05	0.8	0.152	1.9
mil	max	96	185	155	220	7.9	59	12	87
	min	84	160	130	200	2.0	32	6	75

The recommended mounting pad size


MARKING

• SS110